UNIVERSITÀ degli STUDI di CATANIA

DIPARTIMENTO DI FISICA E ASTRONOMIA "ETTORE MAJORANA"

DOTTORATO DI RICERCA IN FISICA

CICLO XXXIV
A. A. 2019 - 2020

Charge transport and devices simulation

2 CFU

Teaching staff
ANTONINO LA MAGNA
Email: Antonino.LaMagna@imm.cnr.it
Office: Zona Industriale VIII Strada 5 I 95121 Catania Italy
Telephone: +39 095 5868220
Reception hours: Friday 11:00-13:00

Program of the course:

Introduction to the quantum and semiclassical charge transport: Ohm law - From semiclassical/continuum to quantum/atomistic formalisms - Contact resistance concept - Landauer formula - bottom-up: one level device.

Quantitative numerical analysis of the quantum carrier dynamics: Charging and self-consistency - Quantum capacitance - Coulomb blockade - Non Equilibrium Green Function - Contact Self Energies- el-ph scattering - perturbative corrections - variational formalism – examples: graphene, nanotubes, atoms' chains.

Boltzmann formalism and semiclassical methods: semiclassical carriers – Boltzmann equation – Scattering kernels - Fermi Golden rule - relaxation times – Phonon scattering – Impurity scattering – charge/charge scattering – Avalanche carriers' generation – Monte Carlo approach – Monte Carlo – Poisson Device simulation – Continuum models – Drift Diffusion models and device simulations – Hydrodynamic models and device simulation – TCAD introduction.

Bibliography:

- S.M. Sze. K. K. Ng "Physics of Semiconductor Devices John Wiley & Sons, Inc."
- K.Tomizawa "Numerical Simulation of Submicron Semiconductor devices" Artech House Inc. Norwood
- S. Datta "Quantum Transport: Atom to Transistor" Cambridge University Press
- S. Datta "Electronic Transport in Mesoscopic Systems" Cambridge University Press